

<b>STN</b>	<b>Polovodičové súčiastky. Elektromechanické mikrosúčiastky. Časť 26: Opis a metódy merania mikrodrážkových a ihlicových štruktúr.</b>	<b>STN EN 62047-26</b>
		35 8792

Semiconductor devices - Micro-electromechanical devices - Part 26: Description and measurement methods for micro trench and needle structures

Táto norma obsahuje anglickú verziu európskej normy.  
This standard includes the English version of the European Standard.

Táto norma bola oznámená vo Vestníku ÚNMS SR č. 09/16

Obsahuje: EN 62047-26:2016, IEC 62047-26:2016

**123439**

**EUROPEAN STANDARD**  
**NORME EUROPÉENNE**  
**EUROPÄISCHE NORM**

**EN 62047-26**

April 2016

ICS 31.080.99

English Version

**Semiconductor devices - Micro-electromechanical devices -  
Part 26: Description and measurement methods for micro trench  
and needle structures  
(IEC 62047-26:2016)**

Dispositifs à semiconducteurs - Dispositifs  
microélectromécaniques - Partie 26: Description et  
méthodes de mesure pour structures de microtranchées et  
de microaiguille  
(IEC 62047-26:2016)

Halbleiterbauelemente - Bauelemente der  
Mikrosystemtechnik - Teil 26: Beschreibung und  
Messverfahren für Mikro-Rillen und Nadelstrukturen  
(IEC 62047-26:2016)

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**European foreword**

The text of document 47F/233/FDIS, future edition 1 of IEC 62047-26, prepared by SC 47F "Micro-electromechanical systems", of IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 62047-26:2016.

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# INTERNATIONAL STANDARD

# NORME INTERNATIONALE



**Semiconductor devices – Micro-electromechanical devices –  
Part 26: Description and measurement methods for micro trench and needle  
structures**

**Dispositifs à semiconducteurs – Dispositifs microélectromécaniques –  
Partie 26: Description et méthodes de mesure pour structures de  
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# INTERNATIONAL STANDARD

# NORME INTERNATIONALE



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**Semiconductor devices – Micro-electromechanical devices –  
Part 26: Description and measurement methods for micro trench and needle  
structures**

**Dispositifs à semiconducteurs – Dispositifs microélectromécaniques –  
Partie 26: Description et méthodes de mesure pour structures de  
microtranchées et de microaiguille**

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ICS 31.080.99

ISBN 978-2-8322-3122-7

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International Standard IEC 62047-26 has been prepared by subcommittee 47F: Microelectromechanical systems, of IEC technical committee 47: Semiconductor devices.

The text of this standard is based on the following documents:

FDIS	Report on voting
47F/233/FDIS	47F/239/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

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**SEMICONDUCTOR DEVICES –  
MICRO-ELECTROMECHANICAL DEVICES –****Part 26: Description and measurement methods for  
micro trench and needle structures****1 Scope**

This part of IEC 62047 specifies descriptions of trench structure and needle structure in a micrometer scale. In addition, it provides examples of measurement for the geometry of both structures. For trench structures, this standard applies to structures with a depth of 1 µm to 100 µm; walls and trenches with respective widths of 5 µm to 150 µm; and aspect ratio of 0,006 7 to 20. For needle structures, the standard applies to structures with three or four faces with a height, horizontal width and vertical width of 2 µm or larger, and with dimensions that fit inside a cube with sides of 100 µm.

This standard is applicable to the structural design of MEMS and geometrical evaluation after MEMS processes.

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